Abstracts

New versatile model: accurate prediction and synthesis ability for arbitrary geometry FET

J. Dubouloy, J.F. Villemazet, V. Grognet, M. Soulard, D. Pasquet and E. Bourdel. "New versatile model: accurate prediction and synthesis ability for arbitrary geometry FET." 1998 MTT-S International Microwave Symposium Digest 98.1 (1998 Vol. I [MWSYM]): 283-286.

An original transistor modeling and synthesis approach, using electromagnetic simulation, is successfully used to describe various FET response. Starting from one single sample, this novel method can predict numerous other device response, which can strongly differ in geometry and gate width. This model shows excellent agreement with experimental data. Other papers have been published on active circuit electromagnetic analysis but, we propose and demonstrate, for the first time, synthesis ability.

☐ Return to main document.

Click on title for a complete paper.